

## 17.5 – 20 GHz 1W AMPLIFIER

- **HIGH RELIABILITY**
- **HIGH DYNAMIC RANGE**
- **COMPACT DESIGN**
- **WIDE BANDWIDTH**

This microwave power amplifier is intended for use in modern solid state communication equipment, where high reliability, high dynamic range, and compact size are important factors. This power amplifier may function as a stand-alone solid-state amplifier or as a driver stage for high power solid state or tube amplifiers. This microwave power amplifier is constructed using Gallium Arsenide FET amplifier stages of high reliability. Each amplifier stage has it's own DC bias circuit for greater stability.

### Typical applications:

- Driver stage in communication equipment.
- Instrumentation.

### Electrical characteristics:

|                                   |                 |
|-----------------------------------|-----------------|
| Frequency Band                    | 17.5 to 20 GHz  |
| RF Power Output (1dB Compression) | + 30 dBm typ.   |
| RF Gain                           | 34 dB typ.      |
| Gain Ripple                       | ± 1.5 dB        |
| Supply Voltage                    | +8 ... +13 V DC |
| Current Consumption               | 1300 mA         |
| Operating temperature range       | - 20 to + 60 °C |

Other frequency and power versions are available upon request.

Specifications are subject to change without notice.

### Outline dimensions (mm):

